# **Hex Unbuffered Inverter**

# **High-Performance Silicon-Gate CMOS**

The MC74HCU04A is identical in pinout to the LS04 and the MC14069UB. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of six single-stage inverters. These inverters are well suited for use as oscillators, pulse shapers, and in many other applications requiring a high-input impedance amplifier. For digital applications, the HC04A is recommended.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V; 2.5 to 6.0 V in Oscillator Configurations
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 12 FETs or 3 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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MARKING DIAGRAMS

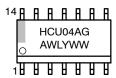


PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

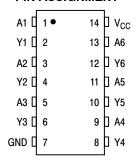
L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

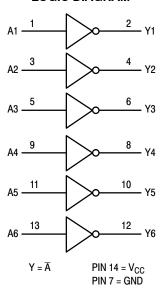
#### **PIN ASSIGNMENT**



# **FUNCTION TABLE**

Inputs	Outputs
A	Y
L H	ΤТ

# **LOGIC DIAGRAM**



#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCU04ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HCU04ADG	SOIC-14	55 Units / Rail
NLV74HCU04ADG*	(Pb-Free)	55 Offits / Hall
MC74HCU04ADR2G	SOIC-14	2500 / Tana & Bool
NLV74HCU04ADR2G*	(Pb-Free)	2500 / Tape & Reel
MC74HCU04ADTR2G		
NLV74HCU04ADTR2G*	(Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — Plastic DIP: -10mW/°C from 65° to 125°C SOIC Package: -7mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	<b>– 55</b>	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	-	No Limit	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			Guara		Guaranteed Lir		
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	–55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 6.0	1.7 2.5 3.6 4.8	1.7 2.5 3.6 4.8	1.7 2.5 3.6 4.8	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 6.0	0.3 0.5 0.8 1.1	0.3 0.5 0.8 1.1	0.3 0.5 0.8 1.1	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = GND$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	1.8 4.0 5.5	1.8 4.0 5.5	1.8 4.0 5.5	V
		$ \begin{aligned}  V_{in} = \text{GND} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 4.0 \text{ mA} \\  I_{out}  \leq 5.2 \text{ mA} \end{aligned} $	4.5	2.36 3.86 5.36	2.26 3.76 5.26	2.20 3.70 5.20	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	–55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{CC}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	0.2 0.5 0.5	0.2 0.5 0.5	0.2 0.5 0.5	V
		$\begin{aligned} V_{in} = V_{CC} &  I_{out}  \leq 2.4 \text{ m/s} \\  I_{out}  \leq 4.0 \text{ m/s} \\  I_{out}  \leq 5.2 \text{ m/s} \end{aligned}$	4.5	0.32 0.32 0.32	0.32 0.37 0.37	0.32 0.40 0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	1	10	40	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50 pF, Input $t_r$ = $t_f$ = 6 ns)

			Gu	aranteed Li	mit	
Symbol	Parameter	v <sub>cc</sub> v	–55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	70 40 14 12	90 45 18 15	105 50 21 18	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Inverter)*	15	рF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>2.</sup> Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

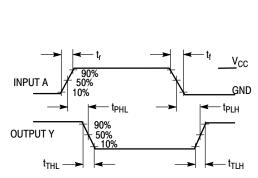
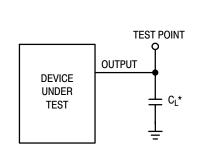


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

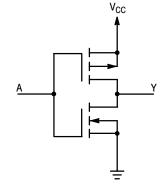


Figure 3. Logic Detail (1/6 of Device Shown)

<sup>1.</sup> For  $V_{CC} = 2.0 \text{ V}$ ,  $V_{out} = 0.2 \text{ V}$  or  $V_{CC} - 0.2 \text{ V}$ .

# **TYPICAL APPLICATIONS**

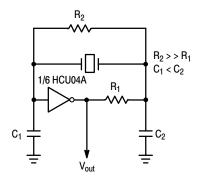


Figure 4. Crystal Oscillator

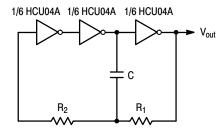


Figure 5. Stable RC Oscillator

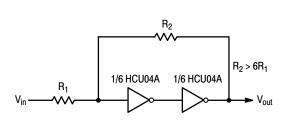


Figure 6. Schmitt Trigger

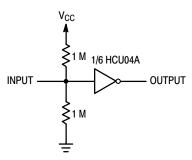


Figure 7. High Input Impedance Single-Stage Amplifier with a 2 to 6 V Supply Range

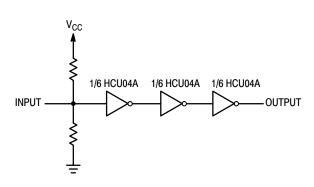
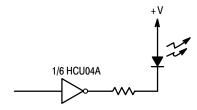


Figure 8. Multi-Stage Amplifier

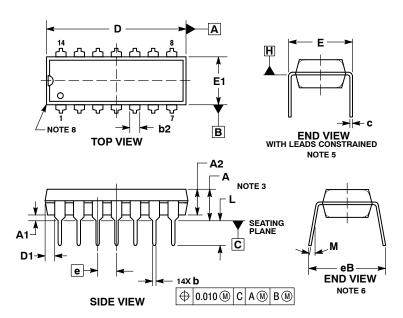


For reduced power supply current, use high-efficiency LEDs such as the Hewlett-Packard HLMP series or equivalent.

Figure 9. LED Driver

#### **PACKAGE DIMENSIONS**

### PDIP-14 CASE 646-06 ISSUE R



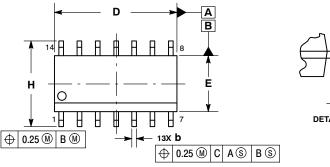
- NOTES:

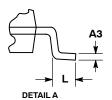
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
  5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
  6. DIMENSION E3 IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
  7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
  8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN MAX MIN		MAX	
Α		0.210		5.33
A1	0.015	-	0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

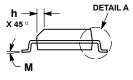
#### **PACKAGE DIMENSIONS**

### SOIC-14 NB CASE 751A-03 ISSUE K









- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.

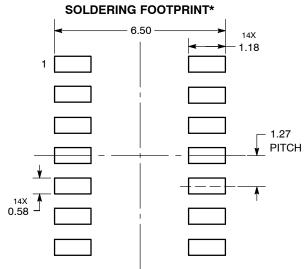
  4. DIMENSIONS D AND E DO NOT INCLUDE

  - MAZIMOW MATERIAL CONDITION:

    4. DIMENSIONS D AND E DO NOT INCLUDE
    MOLD PROTRUSIONS.

    5. MAXIMUM MOLD PROTRUSION 0.15 PER
    SIDE.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049

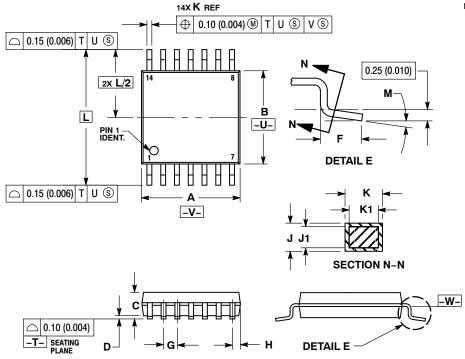


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

### TSSOP-14 **DT SUFFIX** CASE 948G **ISSUE B**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  - DIMENSION B DOES NOT INCLUDE
     INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE
  - DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

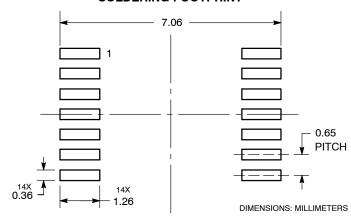
    5. TERMINAL NUMBERS ARE SHOWN FOR

  - REFERENCE ONLY.

    7. DIMENSION A AND B ARE TO BE
    DETERMINED AT DATUM PLANE –W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0 °	8 °	0°	8 °	

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